

Tokuyuki Teraji

List of Publications by Year in descending order

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179
papers

5,809
citations

70961

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69
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181
all docs

181
docs citations

181
times ranked

3705
citing authors

#	ARTICLE	IF	CITATIONS
1	Indistinguishable Photons from Separated Silicon-Vacancy Centers in Diamond. <i>Physical Review Letters</i> , 2014, 113, 113602.	2.9	333
2	Multiple intrinsically identical single-photon emitters in the solid state. <i>Nature Communications</i> , 2014, 5, 4739.	5.8	232
3	All-Optical Initialization, Readout, and Coherent Preparation of Single Silicon-Vacancy Spins in Diamond. <i>Physical Review Letters</i> , 2014, 113, 263602.	2.9	216
4	Phosphorus-doped chemical vapor deposition of diamond. <i>Diamond and Related Materials</i> , 2000, 9, 935-940.	1.8	193
5	Electronic structure of the negatively charged silicon-vacancy center in diamond. <i>Physical Review B</i> , 2014, 89, .	1.1	175
6	Experimental Implementation of Assisted Quantum Adiabatic Passage in a Single Spin. <i>Physical Review Letters</i> , 2013, 110, 240501.	2.9	166
7	Extreme dielectric strength in boron doped homoepitaxial diamond. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	160
8	Perfect alignment and preferential orientation of nitrogen-vacancy centers during chemical vapor deposition diamond growth on (111) surfaces. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	134
9	Hall hole mobility in boron-doped homoepitaxial diamond. <i>Physical Review B</i> , 2010, 81, .	1.1	125
10	Extending spin coherence times of diamond qubits by high-temperature annealing. <i>Physical Review B</i> , 2013, 88, .	1.1	122
11	Photoelectrical imaging and coherent spin-state readout of single nitrogen-vacancy centers in diamond. <i>Science</i> , 2019, 363, 728-731.	6.0	120
12	Isotopically varying spectral features of silicon-vacancy in diamond. <i>New Journal of Physics</i> , 2014, 16, 113019.	1.2	85
13	Homoepitaxial diamond growth by high-power microwave-plasma chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2004, 271, 409-419.	0.7	80
14	Spin properties of dense near-surface ensembles of nitrogen-vacancy centers in diamond. <i>Physical Review B</i> , 2018, 97, .	1.1	76
15	Electronic transitions of electrons bound to phosphorus donors in diamond. <i>Solid State Communications</i> , 2000, 113, 577-580.	0.9	75
16	Photoluminescence excitation spectroscopy of SiV ⁺ and GeV ⁺ color center in diamond. <i>New Journal of Physics</i> , 2017, 19, 063036.	1.2	75
17	Electronic States of Boron and Phosphorus in Diamond. <i>Physica Status Solidi A</i> , 1999, 174, 39-51.	1.7	74
18	Appearance of n-Type Semiconducting Properties of cBN Single Crystals Grown at High Pressure. <i>Japanese Journal of Applied Physics</i> , 2002, 41, L109-L111.	0.8	74

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19	Chemical vapor deposition of homoepitaxial diamond films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 3324-3357.	0.8	73
20	Array of bright silicon-vacancy centers in diamond fabricated by low-energy focused ion beam implantation. <i>Applied Physics Express</i> , 2014, 7, 115201.	1.1	73
21	Highly sensitive UV photodetectors fabricated using high-quality single-crystalline CVD diamond films. <i>Diamond and Related Materials</i> , 2004, 13, 858-862.	1.8	71
22	Low-leakage p-type diamond Schottky diodes prepared using vacuum ultraviolet light/ozone treatment. <i>Journal of Applied Physics</i> , 2009, 105, .	1.1	71
23	Low-temperature spectroscopic study of n-type diamond. <i>Physical Review B</i> , 1999, 59, 14852-14855.	1.1	69
24	Competition between electric field and magnetic field noise in the decoherence of a single spin in diamond. <i>Physical Review B</i> , 2016, 93, .	1.1	69
25	Highly efficient doping of boron into high-quality homoepitaxial diamond films. <i>Diamond and Related Materials</i> , 2006, 15, 602-606.	1.8	68
26	Homoepitaxial diamond film growth: High purity, high crystalline quality, isotopic enrichment, and single color center formation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 2365-2384.	0.8	68
27	Electronic states of phosphorus in diamond. <i>Diamond and Related Materials</i> , 2000, 9, 948-951.	1.8	66
28	Protecting a Diamond Quantum Memory by Charge State Control. <i>Nano Letters</i> , 2017, 17, 5931-5937.	4.5	66
29	Growth of high-quality homoepitaxial CVD diamond films at high growth rate. <i>Journal of Crystal Growth</i> , 2002, 235, 287-292.	0.7	61
30	High-mobility diamond field effect transistor with a monocrystalline h-BN gate dielectric. <i>APL Materials</i> , 2018, 6, .	2.2	59
31	Long coherence time of spin qubits in ^{12}C enriched polycrystalline chemical vapor deposition diamond. <i>Applied Physics Letters</i> , 2012, 101, 012405.	1.5	56
32	Evidence against existing x-ray-energy response theories for silicon-surface-barrier semiconductor detectors. <i>Physical Review A</i> , 1992, 46, R3024-R3027.	1.0	54
33	Microscopic Imaging of the Stress Tensor in Diamond Using in Situ Quantum Sensors. <i>Nano Letters</i> , 2019, 19, 4543-4550.	4.5	51
34	Characterization of boron doped diamond epilayers grown in a NIRIM type reactor. <i>Diamond and Related Materials</i> , 2008, 17, 1330-1334.	1.8	48
35	Transport properties of electron-beam and photo excited carriers in high-quality single-crystalline chemical-vapor-deposition diamond films. <i>Journal of Applied Physics</i> , 2004, 96, 7300-7305.	1.1	47
36	High breakdown voltage Schottky diodes synthesized on p-type CVD diamond layer. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 2088-2092.	0.8	47

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37	High-quality and high-purity homoepitaxial diamond (100) film growth under high oxygen concentration condition. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	47
38	Charge state stabilization of shallow nitrogen vacancy centers in diamond by oxygen surface modification. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 04CK08.	0.8	46
39	Nitrogen-Terminated Diamond Surface for Nanoscale NMR by Shallow Nitrogen-Vacancy Centers. <i>Journal of Physical Chemistry C</i> , 2019, 123, 3594-3604.	1.5	46
40	Ideal Ohmic contact to n-type 6H-SiC by reduction of Schottky barrier height. <i>Applied Physics Letters</i> , 1997, 71, 689-691.	1.5	44
41	Non-destructive detection of killer defects of diamond Schottky barrier diodes. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	44
42	High rate growth and luminescence properties of high-quality homoepitaxial diamond (100) films. <i>Physica Status Solidi A</i> , 2003, 198, 395-406.	1.7	43
43	Lattice location of phosphorus in n-type homoepitaxial diamond films grown by chemical-vapor deposition. <i>Applied Physics Letters</i> , 2001, 79, 3068-3070.	1.5	42
44	High rate growth and electrical/optical properties of high-quality homoepitaxial diamond (100) films. <i>Diamond and Related Materials</i> , 2005, 14, 255-260.	1.8	42
45	Electric Field Breakdown of Lateral Schottky Diodes of Diamond. <i>Japanese Journal of Applied Physics</i> , 2007, 46, L196-L198.	0.8	41
46	Strongly coupled diamond spin qubits by molecular nitrogen implantation. <i>Physical Review B</i> , 2013, 88, .	1.1	41
47	Monte Carlo simulations of electron transport properties of diamond in high electric fields using full band structure. <i>Journal of Applied Physics</i> , 2004, 95, 4866-4874.	1.1	40
48	dc Magnetometry with Engineered Nitrogen-Vacancy Spin Ensembles in Diamond. <i>Nano Letters</i> , 2019, 19, 6681-6686.	4.5	39
49	Low temperature excitation spectrum of phosphorus in diamond. <i>Diamond and Related Materials</i> , 2001, 10, 444-448.	1.8	37
50	Ohmic Contact Formation for N-Type Diamond by Selective Doping. <i>Japanese Journal of Applied Physics</i> , 2003, 42, L882-L884.	0.8	37
51	High-quality boron-doped homoepitaxial diamond grown by high-power microwave-plasma chemical-vapor deposition. <i>Journal of Applied Physics</i> , 2004, 96, 5906-5908.	1.1	37
52	Response function measurement of layered type CVD single crystal diamond radiation detectors for 14â€¢MeV neutrons. <i>Review of Scientific Instruments</i> , 2004, 75, 3581-3584.	0.6	36
53	Highâ€¢temperature stability of Au/pâ€¢type diamond Schottky diode. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009, 3, 211-213.	1.2	36
54	Triple nitrogen-vacancy centre fabrication by C5N4Hn ion implantation. <i>Nature Communications</i> , 2019, 10, 2664.	5.8	33

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55	Improvement in the crystalline quality of homoepitaxial diamond films by oxygen plasma etching of mirror-polished diamond substrates. <i>Journal of Crystal Growth</i> , 2005, 285, 130-136.	0.7	31
56	High-quality homoepitaxial diamond (100) films grown under high-rate growth condition. <i>Diamond and Related Materials</i> , 2005, 14, 1747-1752.	1.8	31
57	Characterization of free-standing single-crystal diamond prepared by hot-filament chemical vapor deposition. <i>Diamond and Related Materials</i> , 2014, 48, 19-23.	1.8	29
58	P-doped diamond grown on (110)-textured microcrystalline diamond: growth, characterization and devices. <i>Journal of Physics Condensed Matter</i> , 2009, 21, 364204.	0.7	28
59	Phonon-assisted electronic transitions in phosphorus-doped n-type chemical vapor deposition diamond films. <i>Diamond and Related Materials</i> , 2001, 10, 439-443.	1.8	27
60	Local stress distribution of dislocations in homoepitaxial chemical vapor deposited single-crystal diamond. <i>Diamond and Related Materials</i> , 2012, 23, 109-111.	1.8	27
61	Model implementation towards the prediction of J(V) characteristics in diamond bipolar device simulations. <i>Diamond and Related Materials</i> , 2014, 43, 34-42.	1.8	26
62	Direct determination of the barrier height of Ti-based ohmic contact on p-type diamond (001). <i>Diamond and Related Materials</i> , 2015, 60, 117-122.	1.8	26
63	Carbon 1s X-ray photoelectron spectra of realistic samples of hydrogen-terminated and oxygen-terminated CVD diamond (111) and (001). <i>Diamond and Related Materials</i> , 2019, 93, 105-130.	1.8	25
64	Ultra-high Performance On-Chip Single Crystal Diamond NEMS/MEMS with Electrically Tailored Self-Sensing Enhancing Actuation. <i>Advanced Materials Technologies</i> , 2019, 4, 1800325.	3.0	25
65	Impact Excitation of Carriers in Diamond under Extremely High Electric Fields. <i>Japanese Journal of Applied Physics</i> , 2001, 40, L715-L717.	0.8	24
66	Ohmic contact for p-type diamond without postannealing. <i>Journal of Applied Physics</i> , 2008, 104, 016104.	1.1	24
67	Effective Use of Source Gas for Diamond Growth with Isotopic Enrichment. <i>Applied Physics Express</i> , 2013, 6, 055601.	1.1	24
68	Electrical Contacts for n-Type Diamond. <i>Japanese Journal of Applied Physics</i> , 1999, 38, L1096-L1098.	0.8	23
69	Hillock-Free Homoepitaxial Diamond (100) Films Grown at High Methane Concentrations. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L216-L219.	0.8	23
70	Polarization- and frequency-tunable microwave circuit for selective excitation of nitrogen-vacancy spins in diamond. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	23
71	Mechanism of reverse current increase of vertical-type diamond Schottky diodes. <i>Journal of Applied Physics</i> , 2017, 122, .	1.1	23
72	Characterization of substrate off-angle effects for high-quality homoepitaxial CVD diamond films. <i>Diamond and Related Materials</i> , 2008, 17, 435-439.	1.8	22

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73	Improved depth resolution of secondary ion mass spectrometry profiles in diamond: A quantitative analysis of the delta-doping. <i>Thin Solid Films</i> , 2014, 557, 222-226.	0.8	21
74	Precise measurements of diamond lattice constant using Bond method. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 111301.	0.8	21
75	Electron emissions from CVD diamond surfaces. <i>Diamond and Related Materials</i> , 2003, 12, 434-441.	1.8	20
76	Further improvement in high crystalline quality of homoepitaxial CVD diamond. <i>Diamond and Related Materials</i> , 2007, 16, 679-684.	1.8	20
77	Schottky barrier height and thermal stability of p-diamond (100) Schottky interfaces. <i>Thin Solid Films</i> , 2014, 557, 241-248.	0.8	20
78	Atomic composition of WC/ and Zr/O-terminated diamond Schottky interfaces close to ideality. <i>Applied Surface Science</i> , 2017, 395, 200-207.	3.1	20
79	Schottky diode architectures on p-type diamond for fast switching, high forward current density and high breakdown field rectifiers. <i>Diamond and Related Materials</i> , 2011, 20, 285-289.	1.8	19
80	Diamond Schottky diodes with ideality factors close to 1. <i>Applied Physics Letters</i> , 2014, 105, 133515.	1.5	19
81	Polarization Transfer to External Nuclear Spins Using Ensembles of Nitrogen-Vacancy Centers. <i>Physical Review Applied</i> , 2021, 15, .	1.5	19
82	Temperature dependent spectroscopic study of the electronic structure of phosphorus in n-type CVD diamond films. <i>Diamond and Related Materials</i> , 2000, 9, 952-955.	1.8	18
83	Proximity-Induced Artefacts in Magnetic Imaging with Nitrogen-Vacancy Ensembles in Diamond. <i>Sensors</i> , 2018, 18, 1290.	2.1	18
84	Lithographically engineered shallow nitrogen-vacancy centers in diamond for external nuclear spin sensing. <i>New Journal of Physics</i> , 2018, 20, 083029.	1.2	18
85	Characterization of phosphorus doped CVD diamond films by cathodoluminescence spectroscopy and topography. <i>Diamond and Related Materials</i> , 2003, 12, 20-25.	1.8	17
86	Fabrication of wrinkled carbon nano-films with excellent field emission characteristics. <i>Diamond and Related Materials</i> , 2005, 14, 2074-2077.	1.8	17
87	Synchronized B and ¹³ C Diamond Delta Structures for an Ultimate In-Depth Chemical Characterization. <i>Applied Physics Express</i> , 2013, 6, 045801.	1.1	17
88	High Output Current Boron-Doped Diamond Metal-Semiconductor Field-Effect Transistors. <i>IEEE Electron Device Letters</i> , 2019, 40, 1748-1751.	2.2	17
89	Dislocations in chemical vapor deposition diamond layer detected by confocal Raman imaging. <i>Journal of Applied Physics</i> , 2020, 128, .	1.1	17
90	Reducing intrinsic energy dissipation in diamond-on-diamond mechanical resonators toward one million quality factor. <i>Physical Review Materials</i> , 2018, 2, .	0.9	17

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91	Ga Ohmic contact for n-type diamond by ion implantation. <i>Applied Physics Letters</i> , 2000, 76, 1303-1305.	1.5	16
92	High-performance diamond soft-X-ray detectors with internal amplification function. <i>Diamond and Related Materials</i> , 2007, 16, 1044-1048.	1.8	16
93	p-type diamond Schottky diodes fabricated by vacuum ultraviolet light/ozon surface oxidation: Comparison with diodes based on wet-chemical oxidation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 2082-2085.	0.8	16
94	New application of NV centers in CVD diamonds as a fluorescent nuclear track detector. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 2641-2644.	0.8	16
95	Imaging of diamond defect sites by electron-beam-induced current. <i>Diamond and Related Materials</i> , 2015, 59, 54-61.	1.8	16
96	A theory on the x-ray sensitivity of a silicon surface-barrier detector including a thermal charge-diffusion effect. <i>Journal of Applied Physics</i> , 1992, 72, 3363-3373.	1.1	15
97	Ohmic Contacts for Phosphorus-Doped n-Type Diamond. <i>Physica Status Solidi A</i> , 2000, 181, 129-139.	1.7	15
98	Boron-Doped Diamond Film Homoepitaxially Grown on High-Quality Chemical-Vapor-Deposited Diamond (100). <i>Japanese Journal of Applied Physics</i> , 2001, 40, 4145-4148.	0.8	14
99	Effects of vicinal angles from (001) surface on the Boron-doping features of high-quality homoepitaxial diamond films grown by the high-power microwave plasma chemical-vapor-deposition method. <i>Journal of Crystal Growth</i> , 2007, 309, 145-152.	0.7	14
100	Direct determination of the barrier height of Au ohmic-contact on a hydrogen-terminated diamond (001) surface. <i>Diamond and Related Materials</i> , 2017, 73, 182-189.	1.8	14
101	Apparent delocalization of the current density in metallic wires observed with diamond nitrogen-vacancy magnetometry. <i>Physical Review B</i> , 2019, 99, .	1.1	14
102	Benchmark for Synthesized Diamond Sensors Based on Isotopically Engineered Nitrogen-Vacancy Spin Ensembles for Magnetometry Applications. <i>Advanced Quantum Technologies</i> , 2020, 3, 2000074.	1.8	14
103	Effect of Deep-Defects Excitation on Mechanical Energy Dissipation of Single-Crystal Diamond. <i>Physical Review Letters</i> , 2020, 125, 206802.	2.9	14
104	Comparison of different methods of nitrogen-vacancy layer formation in diamond for wide-field quantum microscopy. <i>Physical Review Materials</i> , 2020, 4, .	0.9	14
105	Chemical Vapor Deposition of ¹² C Isotopically Enriched Polycrystalline Diamond. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 090104.	0.8	13
106	Fluorescence Polarization Switching from a Single Silicon Vacancy Colour Centre in Diamond. <i>Scientific Reports</i> , 2015, 5, 12244.	1.6	13
107	Nonvanishing effect of detuning errors in dynamical-decoupling-based quantum sensing experiments. <i>Physical Review A</i> , 2019, 99, .	1.0	13
108	Operations of hydrogenated diamond metal-oxide semiconductor field-effect transistors after annealing at 500 Å°C. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 315104.	1.3	13

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109	The Electronic Structure of Phosphorus in n-Type CVD Diamond Films: Revised. <i>Physica Status Solidi A</i> , 2000, 181, 11-16.	1.7	12
110	Electric field breakdown of lateral-type Schottky diodes formed on lightly doped homoepitaxial diamond. <i>Applied Surface Science</i> , 2008, 254, 6273-6276.	3.1	12
111	Near-Surface Defects in Boron-Doped Diamond Schottky Diodes Studied From Capacitance Transients. <i>Applied Physics Express</i> , 0, 1, 035003.	1.1	12
112	Localized mid-gap-states limited reverse current of diamond Schottky diodes. <i>Journal of Applied Physics</i> , 2012, 111, 104503.	1.1	12
113	Dislocation analysis of homoepitaxial diamond (001) film by x-ray topography. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 045503.	0.8	12
114	Equilibrium charge state of NV centers in diamond. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	12
115	Pinning-controlled ohmic contacts: application to SiC(0001). <i>Applied Surface Science</i> , 1996, 107, 218-221.	3.1	11
116	Photocurrent and optical absorption spectroscopic study of n-type phosphorus-doped CVD diamond. <i>Diamond and Related Materials</i> , 1999, 8, 882-885.	1.8	11
117	Thermal stabilization and deterioration of the WC/p-type diamond (100) Schottky barrier interface. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 2363-2366.	0.8	11
118	Direct observation of the leakage current in epitaxial diamond Schottky barrier devices by conductive-probe atomic force microscopy and Raman imaging. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 355102.	1.3	11
119	Investigation of the silicon vacancy color center for quantum key distribution. <i>Optics Express</i> , 2015, 23, 32961.	1.7	11
120	Characteristic Luminescence Correlated with Leaky Diamond Schottky Barrier Diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1700180.	0.8	11
121	Reducing energy dissipation and surface effect of diamond nanoelectromechanical resonators by annealing in oxygen ambient. <i>Carbon</i> , 2017, 124, 281-287.	5.4	11
122	Field-induced effects of implanted Ga on high electric field diamond devices fabricated by focused ion beam. <i>Applied Surface Science</i> , 2003, 216, 65-71.	3.1	10
123	Development of a charge-carrier drift velocity measurement system in diamonds by using a UV pulse laser. <i>Diamond and Related Materials</i> , 2005, 14, 1992-1994.	1.8	10
124	Isotopic identification of engineered nitrogen-vacancy spin qubits in ultrapure diamond. <i>Physical Review B</i> , 2014, 90, .	1.1	10
125	Nitrogen-vacancy centers created by N ⁺ ion implantation through screening SiO ₂ layers on diamond. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	10
126	Plasma etching phenomena in heavily boron-doped diamond growth. <i>Diamond and Related Materials</i> , 2017, 76, 38-43.	1.8	10

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127	Effect of Annealing Temperature on Performances of Boron-Doped Diamond Metal-Insulator-Semiconductor Field-Effect Transistors. IEEE Transactions on Electron Devices, 2020, 67, 1680-1685.	1.6	10
128	Boron-Doped Diamond MOSFETs With High Output Current and Extrinsic Transconductance. IEEE Transactions on Electron Devices, 2021, 68, 3963-3967.	1.6	10
129	Magnetic noise from ultrathin abrasively deposited materials on diamond. Physical Review Materials, 2018, 2, .	0.9	10
130	Formation of self-assembled platinum particles on diamond and their embedding in diamond by microwave plasma chemical vapor depositions. Diamond and Related Materials, 2006, 15, 1544-1549.	1.8	9
131	Electrical properties of diamond n-i-p structures at high electric fields. Applied Surface Science, 2005, 244, 310-313.	3.1	8
132	Development of a TOF measurement system of charge carrier dynamics in diamond thin films using a UV pulsed laser. Diamond and Related Materials, 2006, 15, 1921-1925.	1.8	8
133	Deep levels in homoepitaxial boron-doped diamond films studied by capacitance and current transient spectroscopies. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2179-2183.	0.8	8
134	Homoepitaxial diamond chemical vapor deposition for ultra-light doping. Materials Science in Semiconductor Processing, 2017, 70, 197-202.	1.9	8
135	Detection of Defects in Diamond by Etch-Pit Formation. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900247.	0.8	8
136	Fabrication of diamond n-i-p structures and their electrical and electroluminescence properties under high electric fields. Diamond and Related Materials, 2007, 16, 112-117.	1.8	7
137	Effect of Magnetic Field on Phosphorus Centre in Diamond. Physica Status Solidi A, 2001, 186, 291-295.	1.7	6
138	Room-temperature growth of single-crystalline TiO ₂ thin films on nanometer-scaled substrates by dc magnetron sputtering deposition. Journal of Crystal Growth, 2007, 299, 349-357.	0.7	6
139	High quality n-type chemical vapor deposited {111}-oriented diamonds: Growth and fabrication of related electrical devices. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1978-1981.	0.8	6
140	Isotopic enrichment of diamond using microwave plasma-assisted chemical vapor deposition with high carbon conversion efficiency. Thin Solid Films, 2014, 557, 231-236.	0.8	6
141	Chemical Vapor Deposition of ¹² C Isotopically Enriched Polycrystalline Diamond. Japanese Journal of Applied Physics, 2012, 51, 090104.	0.8	6
142	Charge stability of shallow single nitrogen-vacancy centers in lightly boron-doped diamond. Carbon, 2022, 192, 473-481.	5.4	6
143	Propagation of dislocations in diamond (111) homoepitaxial layer. Journal of Applied Physics, 2022, 132, .	1.1	5
144	Interface formation and properties of ¹⁵ N-NPD thermally deposited on CVD diamond films. Applied Surface Science, 2003, 216, 106-112.	3.1	4

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145	Characterization of $\hat{\pm}$ -NPD Thermally Deposited on Hydrogen-Terminated Single-Crystal Chemical-Vapor-Deposited Diamond Films. Japanese Journal of Applied Physics, 2003, 42, 5233-5238.	0.8	4
146	Growth and characterization of P-doped CVD diamond (111) thin films homoepitaxially grown using trimethylphosphine. Applied Surface Science, 2005, 244, 305-309.	3.1	4
147	Lattice vibrations of single and multi-layer isotopologic graphene. Carbon, 2018, 140, 449-457.	5.4	4
148	Spin coherence and depths of single nitrogen-vacancy centers created by ion implantation into diamond via screening masks. Journal of Applied Physics, 2020, 127, 244502.	1.1	4
149	Effect of surface irregularities on diamond Schottky barrier diode with threading dislocations. Diamond and Related Materials, 2022, 127, 109188.	1.8	4
150	Hydrogen-related structural changes on CVD diamond (1 0 0) surfaces by ultra-high-vacuum annealing. Applied Surface Science, 2003, 216, 59-64.	3.1	3
151	Development of Layered Type Single Crystalline Diamond Radiation Detector as an Energy Spectrometer. Journal of Nuclear Science and Technology, 2008, 45, 391-394.	0.7	3
152	Forward tunneling current in {111}-oriented homoepitaxial diamond p-n junction. Diamond and Related Materials, 2012, 21, 33-36.	1.8	3
153	Reprint of "Imaging of diamond defect sites by electron-beam-induced current". Diamond and Related Materials, 2016, 63, 30-37.	1.8	3
154	Determining the position of a single spin relative to a metallic nanowire. Journal of Applied Physics, 2021, 129, .	1.1	3
155	Long gap spark discharge ignition using a boron-doped diamond electrode. Journal Physics D: Applied Physics, 2021, 54, 405204.	1.3	3
156	Impact ionization phenomenon in single-crystalline rutile TiO ₂ . Applied Surface Science, 2005, 244, 394-398.	3.1	2
157	Different behaviors of F ⁺ centers due to electron beam irradiations between synthetic sapphire and Be-diffusion-treated natural sapphire. Journal of Crystal Growth, 2006, 292, 546-549.	0.7	2
158	Effects of shallow traps on the reverse current of diamond Schottky diode: An electrical transient study. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1460-1463.	0.8	2
159	Comprehensive nanoscopic analysis of tungsten carbide/Oxygenated-diamond contacts for Schottky barrier diodes. Applied Surface Science, 2021, 537, 147874.	3.1	2
160	Distinguishing dislocation densities in intrinsic layers of pin diamond diodes using two photon-excited photoluminescence imaging. Diamond and Related Materials, 2021, 117, 108463.	1.8	2
161	Charge transfer between thermally deposited $\hat{\pm}$ -naphthyl-phenyl-diamine and chemical-vapor-deposited homoepitaxial diamond films. Applied Physics Letters, 2003, 83, 4776-4778.	1.5	1
162	Interfacial charge transfer and hole injection in $\hat{\pm}$ -NPD organic overlayer-CVD diamond substrate system. Applied Surface Science, 2004, 237, 470-477.	3.1	1

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163	Fabrication of nano-sized platinum particles self-assembled on and in CVD diamond films. Applied Surface Science, 2004, 237, 489-494.	3.1	1
164	Diamond bipolar device simulation. , 2013, , .		1
165	Deterministic doping to silicon and diamond materials for quantum processing. , 2016, , .		1
166	Displacement current of Au/p-diamond Schottky contacts. Materials Science in Semiconductor Processing, 2017, 70, 207-212.	1.9	1
167	Ultrapure homoepitaxial diamond films grown by chemical vapor deposition for quantum device application. Semiconductors and Semimetals, 2020, 103, 37-55.	0.4	1
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